

L Number	Hits	Search Text	DB	Time stamp
-	4390	(438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:02
-	1235	(257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:02
-	5515	((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:03
-	60702	(amorphous or alpha) adj2 (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:04
-	36998	a\$lsi or a\$lsilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:04
-	90362	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:31
-	718	((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and ((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:05
-	6117	salicide or (self adj3 align\$5 adj3 silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 17:34
-	60696	silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:06
-	7978	poly\$1metal or polycide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:07
-	64299	(salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:07
-	510	((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and ((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:07
-	8836	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:09

-	894622	gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:09
-	422	((((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide))) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:09
-	6905	(((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide))) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:10
-	6905	((((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide))) and gate) or (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide))) and gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:11
-	583446	spacer or sidewall	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 17:33
-	3702	(((((((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide))) and gate) or (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide))) and gate)) and (spacer or sidewall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:12
-	494824	drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:12
-	3250	(((((((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide))) and gate) or (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide))) and gate)) and (spacer or sidewall)) and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:12

-	117154	gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:22
-	2798	(((((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and gate) or (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and gate)) and (spacer or sidewall)) and drain) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:17
-	3204180	w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:30
-	2622	(((((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and gate) or (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and gate)) and (spacer or sidewall)) and drain) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5))) and (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:19
-	49712	wet with etch\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:19
-	1173	(((((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and gate) or (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and gate)) and (spacer or sidewall)) and drain) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5))) and (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum)) and (wet with etch\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:20

-	9379	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:22
-	2387	((((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with gate) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:22
-	124844	gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5 or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:23
-	2227	(((((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with gate) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5 or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:23
-	87822	(w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:24
-	1532	(((((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with gate) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5 or dielectric))) and ((w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) with gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:24
-	849	((((((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with gate) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5 or dielectric))) and ((w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) with gate)) and (spacer or sidewall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:25
-	1184	((((((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with gate) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5 or dielectric))) and ((w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) with gate)) and (spacer or sidewall)) or (((((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and ((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:25
-	633335	fet or mos\$lfet or mis\$lfet or mos or pmos or nmos or cmos or field adj6 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:27

-	1044	(((((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with gate) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5 or dielectric))) and ((w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) with gate)) and (spacer or sidewall)) or (((((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and gate)) and (fet or mos\$lfet or mis\$lfet or mos or pmos or nmos or cmos or field adj6 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:28
-	3271	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) same (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:31
-	2842	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) same (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) same gate) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5 or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:32
-	1031	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) same (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) same gate) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5 or dielectric))) and (spacer or sidewall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:32
-	1205	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) same (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) same gate) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5 or dielectric))) and (spacer or sidewall)) and (fet or mos\$lfet or mis\$lfet or mos or pmos or nmos or cmos or field adj6 transistor)) or (((((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$metal or polycide))) and gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:33
-	841	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) same (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) same gate) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5 or dielectric))) and (spacer or sidewall)) and (fet or mos\$lfet or mis\$lfet or mos or pmos or nmos or cmos or field adj6 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:34
-	67570	tft or (thin adj3 film adj3 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:35

-	900	(((((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) same (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) same gate) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5 or dielectric))) and (spacer or sidewall)) and (fet or mos\$lfet or mis\$lfet or mos or pmos or nmos or cmos or field adj6 transistor)) or (((((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and ((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide))) and gate)) not (tft or (thin adj3 film adj3 transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:41
-	44146	unreact\$5 with (remov\$5 or etch\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 17:31
-	259	(((((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) same (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) same gate) and (gate adj3 (oxide or dioxide or "sio.sub.2" or insulat\$5 or dielectric))) and (spacer or sidewall)) and (fet or mos\$lfet or mis\$lfet or mos or pmos or nmos or cmos or field adj6 transistor)) or (((((438/652 or 438/655 or 438/656 or 438/657 or 438/664).ccls.) or ((257/e21.162 or 257/e21.166 or 257/e21.195 or 257/e21.202).ccls.)) and ((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and ((salicide or (self adj3 align\$5 adj3 silicide)) or silicide or (poly\$1metal or polycide))) and gate)) not (tft or (thin adj3 film adj3 transistor))) and (unreact\$5 with (remov\$5 or etch\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 14:42
-	49397	high adj3 (dielectric or k)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 17:35
-	3076	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with (form\$6 or deposit\$6) with (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 17:30
-	953	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with (form\$6 or deposit\$6) with (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum)) same gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 17:32
-	355	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with (form\$6 or deposit\$6) with (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum)) same gate) and (spacer or sidewall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 17:33
-	64815	salicide or self adj3 align\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 17:34

-	158	(((((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with (form\$6 or deposit\$6) with (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) same gate) and (spacer or sidewall)) and (salicide or self adj3 align\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 17:35
-	15	(((((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with (form\$6 or deposit\$6) with (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) same gate) and (spacer or sidewall)) and (salicide or self adj3 align\$5)) and (high adj3 (dielectric or k))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 17:42
-	386150	barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 17:42
-	152	(((((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) same (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) same gate) same barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 17:45
-	61	(((((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) same (w or tungsten or mo or molybdenum or ti or titanium or ta or tantalum) same gate) same barrier) and (salicide or self adj3 align\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 18:07
-	9852	metal adj2 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 18:07
-	1801	(metal adj2 gate) and (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 18:07
-	149	((metal adj2 gate) and (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon))) and (unreact\$5 with (remov\$5 or etch\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 18:08
-	25	((("6475874") or ("6503833") or ("6534390") or ("6436840") or ("6440868") or ("6326251") or ("6084279") or ("6475908") or ("6429109") or ("5625217") or ("5789312") or ("6100188") or ("6326251")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/26 13:16
-	90453	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:32
-	15403	lp\$1cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:32
-	14771	pe\$1cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:33
-	1447	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with lp\$1cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/27 12:33

-	1103	((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with pe\$lcvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/27 12:33
-	245	(((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with lp\$lcvd) and (((amorphous or alpha) adj2 (si or silicon)) or (a\$lsi or a\$lsilicon)) with pe\$lcvd)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/27 12:33